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| Substitute for Form 1449A/PTO | Application Number | 10/661, 130 | | | |
| INFORMATION DISCLOSURE | Filing Date | 9/12/2003 | | | |
| STATEMENT BY APPLICANT | First Named Inventor | Visokay et al. | | | |
| | Group Art Unit | 2825 | | | |
| (use as many sheets as necessary) | Examiner Name | MALSAWMA | | | |

Attorney Docket No.

TI-35942

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US and Foreign Patent Documents: ¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the fwo-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁵Applicant is to place a check mark here if English language Translation is attached.

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